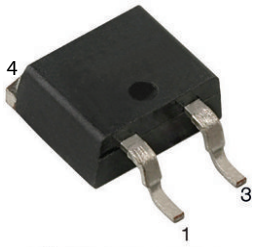
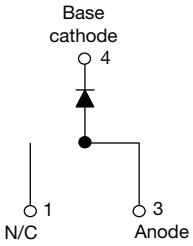
Hyperfast Rectifier, 20 A FRED Pt® G5



D²PAK 2L (TO-263AB 2L)



LINKS TO ADDITIONAL RESOURCES

3D Models

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	20 A
V_R	600 V
V_F at I_F at 125 °C	1.23 V
t_{rr} (typ.)	22 ns
T_J max.	175 °C
Package	D²PAK 2L (TO-263AB 2L)
Circuit configuration	Single

FEATURES

- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)
Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Repetitive peak reverse voltage	V_{RRM}		600	V
Average rectified forward current	$I_{F(AV)}$	T_C = 119 °C, D = 0.50	20	A
Repetitive peak forward current	I_{FRM}	T_C = 119 °C, D = 0.50, f = 20 kHz	40	
Non-repetitive peak surge current	I_{FSM}	T_C = 25 °C, t_p = 10 ms, sine wave	200	
Operating junction and storage temperature	T_J, T_{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	I_R = 100 µA	600	-	-	V
Forward voltage	V_F	I_F = 20 A	-	1.37	1.68	
		I_F = 20 A, T_J = 125 °C	-	1.23	-	
Reverse leakage current	I_R	V_R = V_R rated	-	-	10	µA
		T_J = 125 °C, V_R = V_R rated	-	-	500	
Junction capacitance	C_T	V_R = 200 V	-	25	-	pF
Series inductance	L_S	Measured to lead 5 mm from package body	-	8	-	nH

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	I_F = 1.0 A, dI_F/dt = 100 A/µs, V_R = 30 V		-	22	-	ns
		T_J = 25 °C	I_F = 12 A dI_F/dt = 1000 A/µs V_R = 400 V	-	39	-	
		T_J = 125 °C		-	49	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	15	-	A
		T_J = 125 °C		-	23	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	290	-	nC
		T_J = 125 °C		-	730	-	
Reverse recovery time	t_{rr}	T_J = 25 °C	I_F = 20 A dI_F/dt = 1000 A/µs V_R = 400 V	-	47	-	ns
		T_J = 125 °C		-	62	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	15	-	A
		T_J = 125 °C		-	23	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	400	-	nC
		T_J = 125 °C		-	1000	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R_{thJC}		-	-	1.72	°C/W
Weight			-	2.0	-	g
			-	0.07	-	oz.
Maximum junction and storage temperature range	T_J, T_{Stg}		-55	-	175	°C
Marking device		Case style D^2PAK 2L (TO-263AB 2L)	E5TH2106SH			

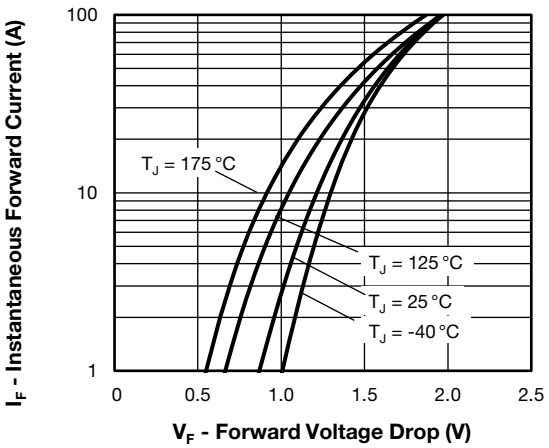


Fig. 1 - Forward Voltage Drop Characteristics

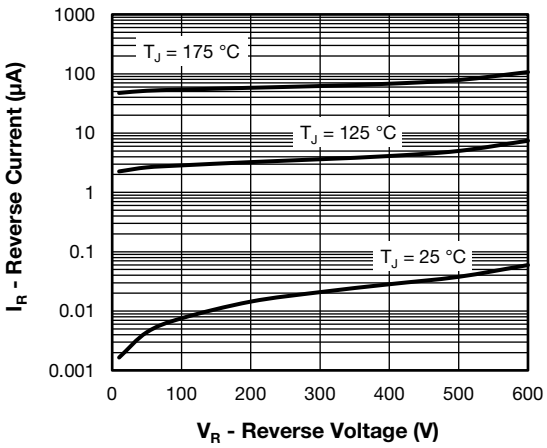


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

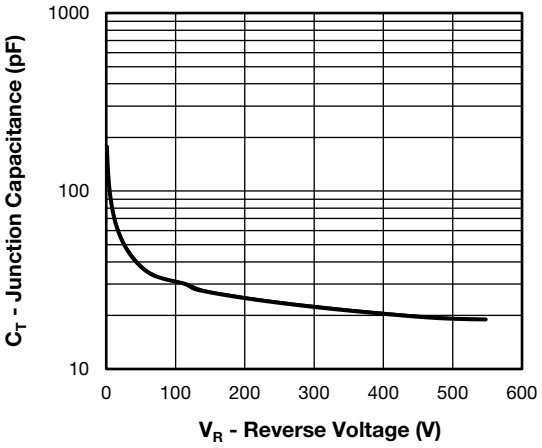


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

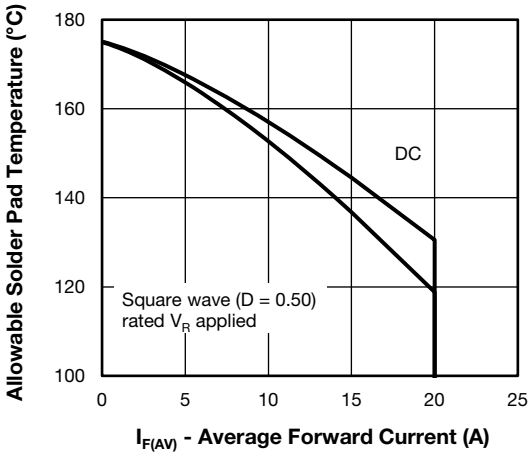


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

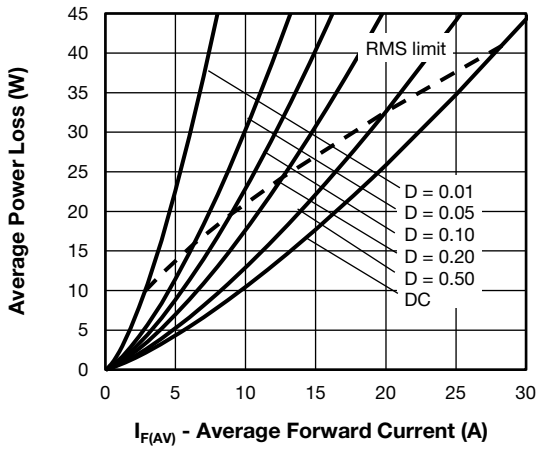


Fig. 5 - Forward Power Loss Characteristics

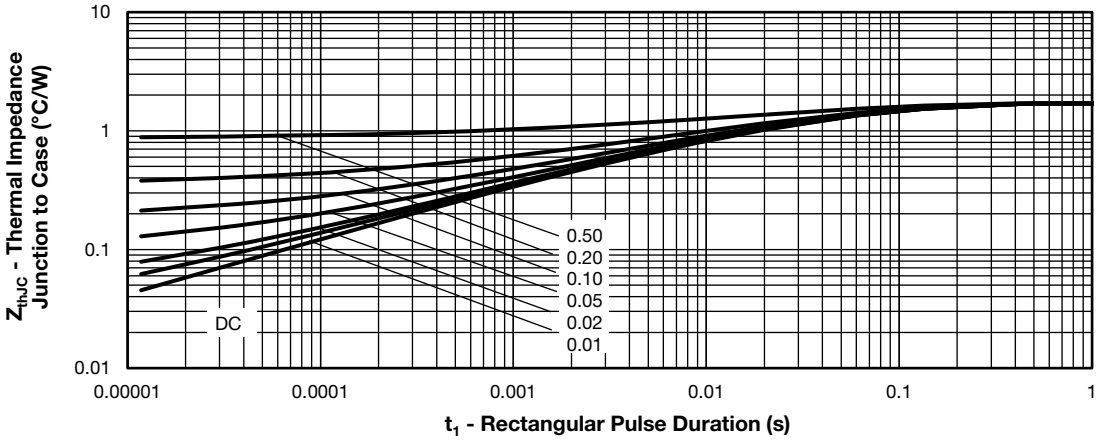


Fig. 6 - Transient Thermal Impedance, Junction to Case

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

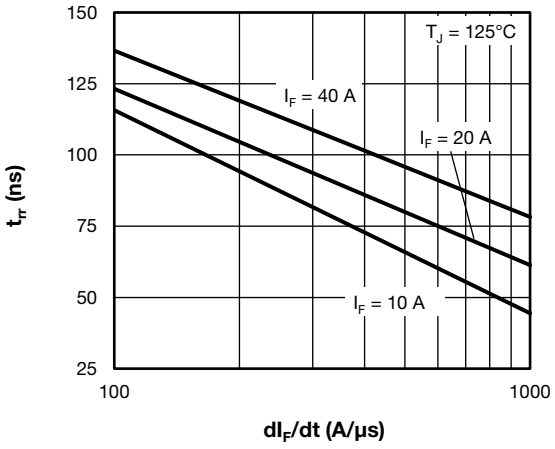


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

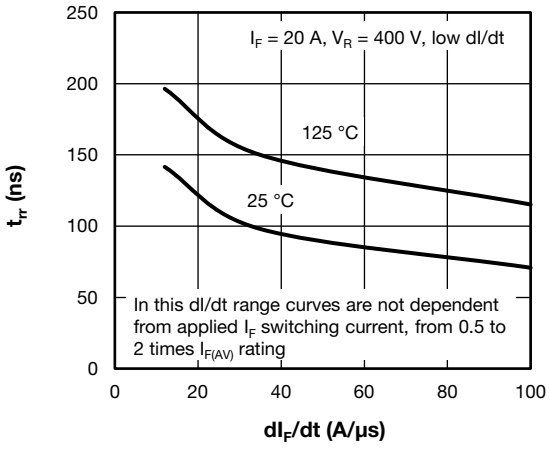


Fig. 10 - Typical Reverse Recovery Time vs. dI_F/dt

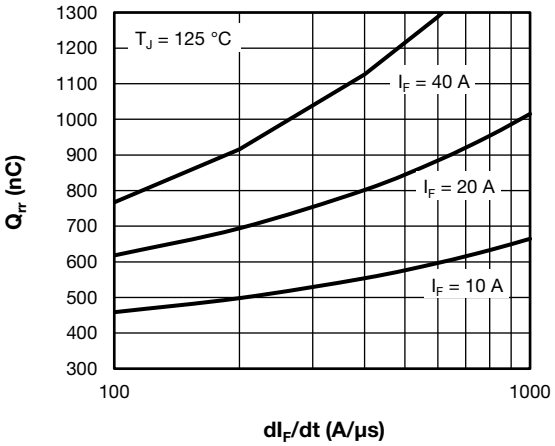


Fig. 8 - Typical Reverse Recovery Charge vs. dI_F/dt

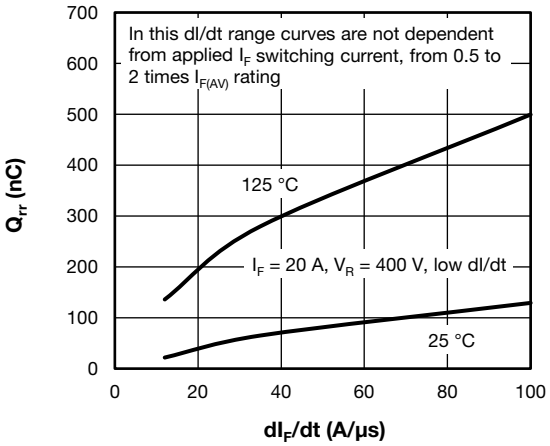


Fig. 11 - Typical Reverse Recovery Charge vs. dI_F/dt

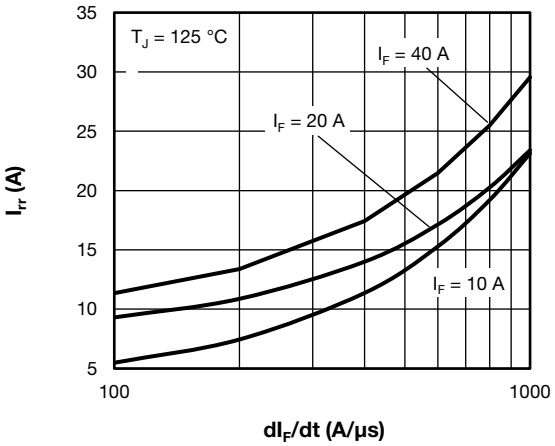


Fig. 9 - Typical Reverse Recovery Current vs. dI_F/dt

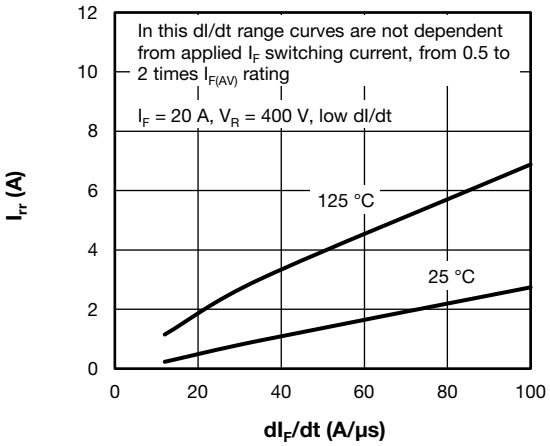


Fig. 12 - Typical Reverse Recovery Current vs. dI_F/dt

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

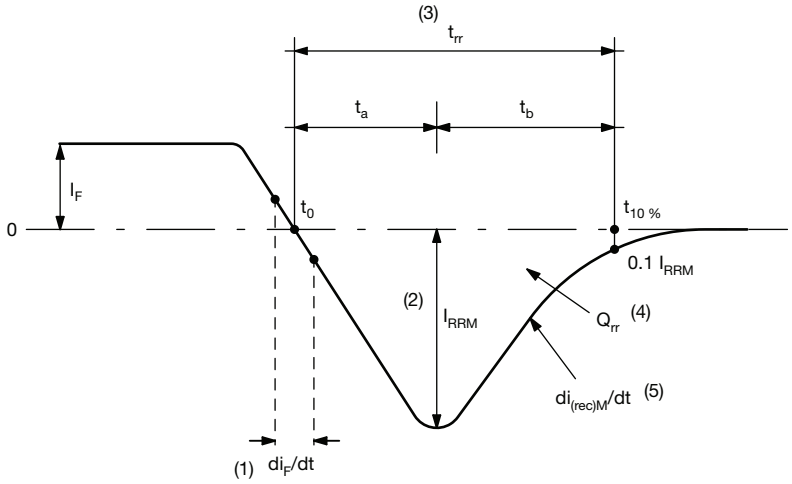


Fig. 13 - Reverse Recovery Waveform and Definitions

Notes

(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from t_0, crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM}

(4) Q_{rr} - area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0}^{t_{10\ \%}} I(t)dt$$

(5) $di_{(rec)}M/dt$ - peak rate of change of current during t_b portion of t_{rr}

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

ORDERING INFORMATION TABLE

Device code

VS-	E	5	T	H	21	06	S2	L	H	M3
1	2	3	4	5	6	7	8	9	10	11

1 - Vishay Semiconductors product

2 - E = single diode

3 - 5 = FRED generation 5

4 - Package:
T = D^2PAK (TO-263) package

5 - H = hyperfast recovery

6 - Current rating (21 = 20 A)

7 - Voltage rating (06 = 600 V)

8 - S2 = true 2 pin D^2PAK

9 - None = tube (50 pieces)
- L = tape and reel (left oriented, for D^2PAK package)
If needed different orientation/packaging, please contact factory

10 - H = AEC-Q101 qualified

11 - Environmental digit:
M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

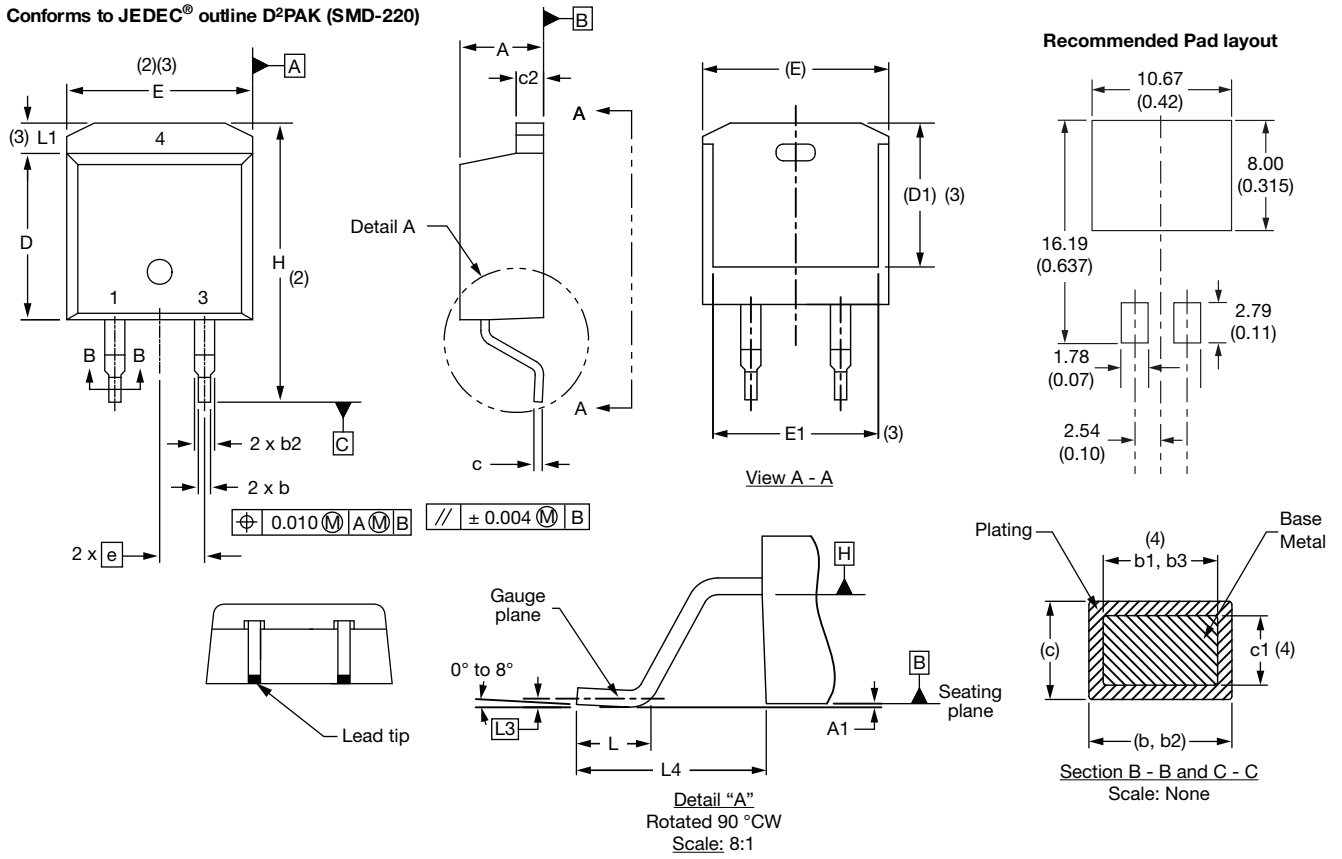
ORDERING INFORMATION (Example)		
PREFERRED P/N	**BASE QUANTITY**	**PACKAGING DESCRIPTION**
VS-E5TH2106S2LHM3	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96683
Part marking information	www.vishay.com/doc?96693
Packaging information	www.vishay.com/doc?95032

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

D^2PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
c	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100 BSC		
H	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

(1) Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2026 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000